

Transverse thermoelectric effect in *a*-axis inclinedly oriented

SnSe thin films

(SUPPLEMENTARY MATERIAL)

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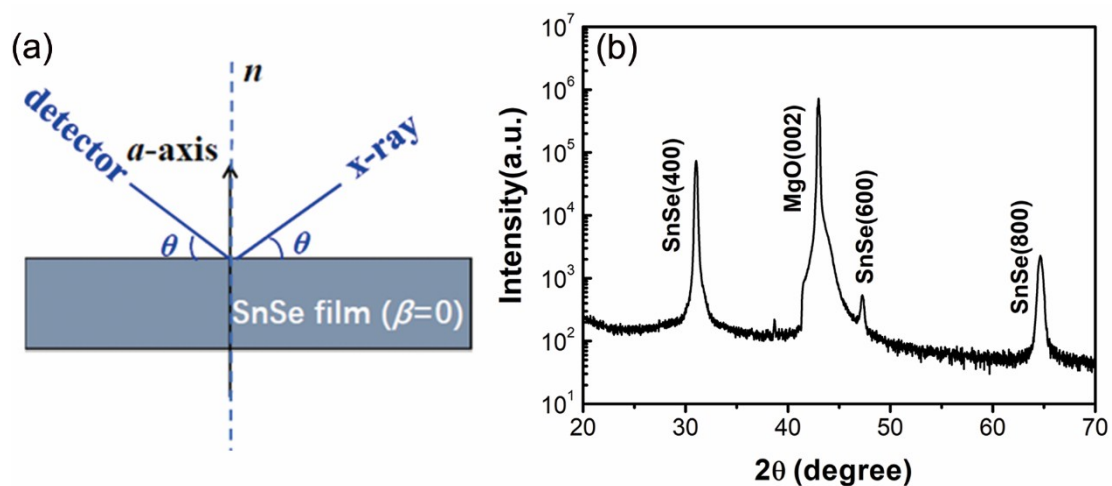


Fig. S1. (a) XRD pattern of the *a*-axis oriented SnSe thin film ($\beta=0^\circ$) deposited on MgO single crystal substrate. (b) The left hand is the sketch map of the XRD measurement.

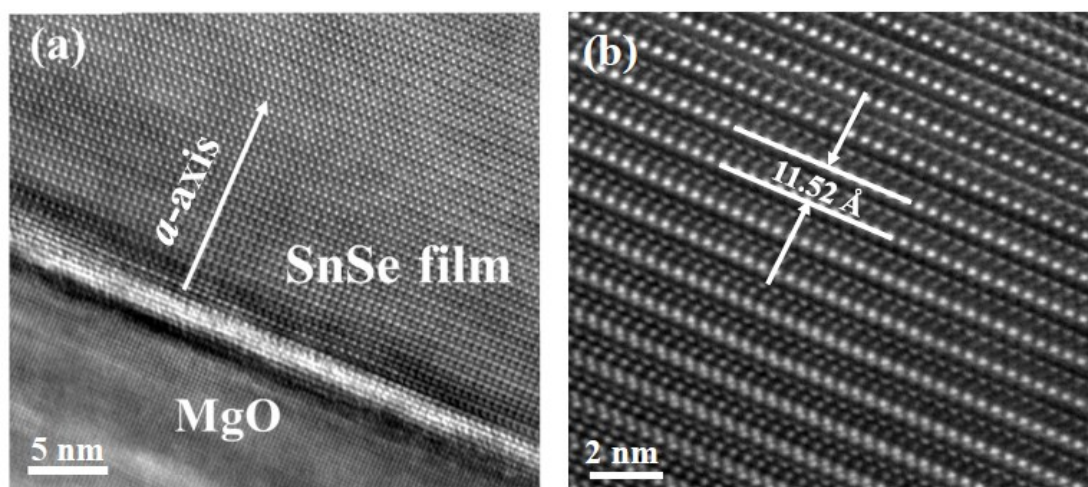


Fig. S2. (a) HRTEM cross-sectional image of the SnSe thin film on MgO single crystal substrate; (b) the magnified HRTEM image of the film part, showing that the *a*-lattice parameter is about 11.52 Å